

Description

The HD6365 uses advanced trench technology to provide excellent $R_{\text{DS(ON)}}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a

Battery protection or in other Switching application.

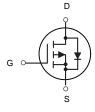


TO252-2L

General Features

 $V_{DS} = -30V I_{D} = -120A$

 $R_{DS(ON)}$ <4.5m Ω @ V_{GS} =-10V



P-Channel MOSFET

Application

Lithium battery protection

Wireless impact

Mobile phone fast charging

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)	
HD6365	TO252-2L	HD6365 XXX YYYY	2500	

Absolute Maximum Ratings (TC=25°Cunless otherwise noted)

Symbol	Parameter	Max.	Units	
VDSS	Drain-Source Voltage	-30	V	
VGSS	Gate-Source Voltage	±20	V	
ID	Continuous Drain Current $T_C = 25^{\circ}C$ -120		А	
ID	Continuous Drain Current T _C = 100 ℃	-80	А	
IDM	Pulsed Drain Current note1	-470	А	
EAS	Single Pulsed Avalanche Energy note2	580	mJ	
PD	Power Dissipation T _C = 25 °C 100		W	
R0JC	Thermal Resistance, Junction to Case 1.4		°C/W	
TJ, TSTG	Operating and Storage Temperature Range	mperature Range -55 to +175 °C		



Electrical Characteristics (TJ=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
On/Off States						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =-250μA	-30			V
IDSS	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V			-1	μA
Igss	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1	-1.7	-2.5	V
g FS	Forward Transconductance	V _{DS} =-5V, I _D =-20A		65		S
Б	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-20A		3.7	4.5	mΩ
R _{DS} (ON)		V _{GS} =-4.5V, I _D =-20A		6	8.2	mΩ
Dynamic Chara	cteristics					
Ciss	Input Capacitance			7000		pF
Coss	Output Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1.0MHz		820		pF
Crss	Reverse Transfer Capacitance			540		pF
Rg	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1.0MHz		2.2		Ω
Switching Para	meters	,		1		
t _{d(on)}	Turn-on Delay Time			14		nS
tr	Turn-on Rise Time	V _{GS} =-10V, V _{DS} =-15V,		13		nS
$t_{d(off)}$	Turn-Off Delay Time	RL=0.75 Ω , R _{GEN} =3 Ω		65		nS
t _f	Turn-Off Fall Time			37		nS
Qg	Total Gate Charge			130		nC
Qgs	Gate-Source Charge	V _{GS} =-10V, V _{DS} =-15V, I _D =-20A		12		nC
Q_{gd}	Gate-Drain Charge			31		nC
Source-Drain D	iode Characteristics	,		1		
I _{SD}	Source-Drain Current (Body Diode)				-108	Α
V _{SD}	Forward on Voltage (Note 3)	V _{GS} =0V, I _S =-20A -1.2		-1.2	V	
t _{rr}	Reverse Recovery Time	I _F =-20A, di/dt=100A/μs 30			ns	
Qrr	Reverse Recovery Charge	I _F =-20A, di/dt=100A/μs		40		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature. Notes 2.E_{AS} condition: T_J =25°C, V_{DD} =15V, V_G =-10V, Rg=25 Ω , L=0.5mH.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



Typical Electrical And Thermal Characteristics (Curves)

Figure 1. Output Characteristics

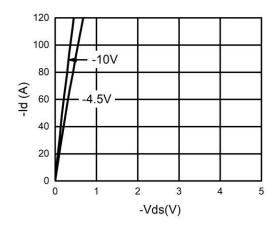


Figure 2. Transfer Characteristics

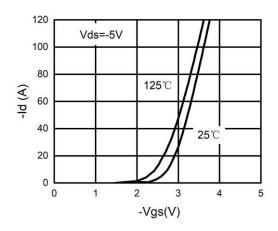


Figure 3. Power Dissipation

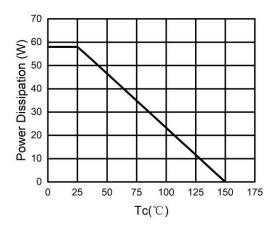


Figure 4. Drain Current

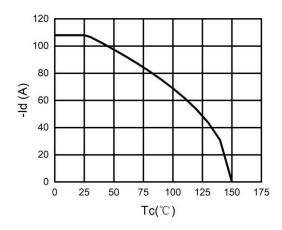


Figure 5. BV_{DSS} vs Junction Temperature

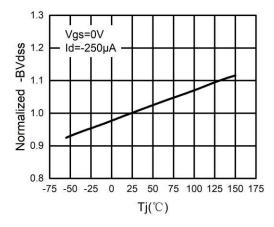


Figure 6. R_{DS(ON)} vs Junction Temperature

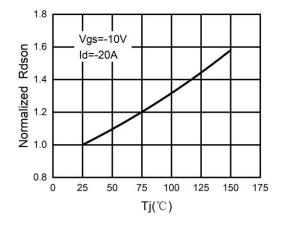




Figure 7. Gate Charge Waveforms

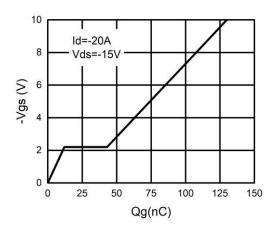


Figure 8. Capacitance

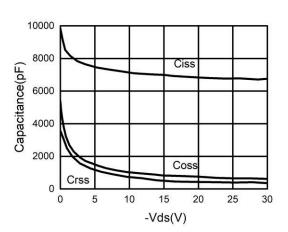


Figure 9. Body-Diode Characteristics

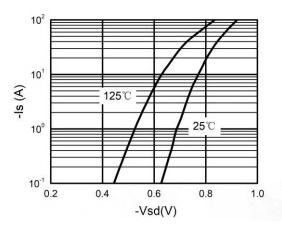
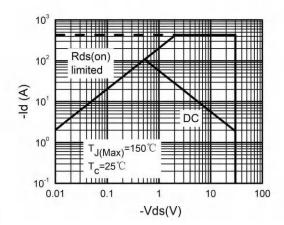
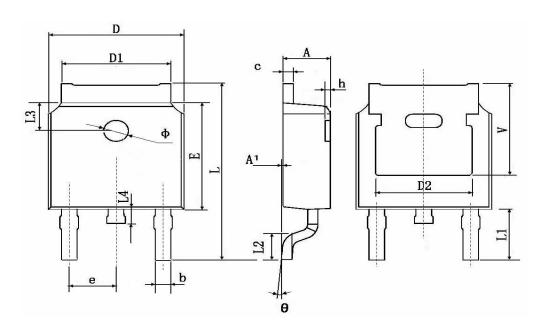


Figure 10. Maximum Safe Operating Area





TO252-2L Package Information



Dimensions In Millimeters		Dimensions In Inches		
Min.	Max.	Min.	Max.	
2.200	2.400	0.087	0.094	
0.000	0.127	0.000	0.005	
0.660	0.860	0.026	0.034	
0.460	0.580	0.018	0.023	
6.500	6.700	0.256	0.264	
5.100	5.460	0.201	0.215	
4.830 TYP.		0.190 TYP.		
6.000	6.200	0.236	0.244	
2.186	2.386	0.086	0.094	
9.800	10.400	0.386	0.409	
2.900 TYP.		0.114 TYP.		
1.400	1.700	0.055	0.067	
	1.600 TYP.		0.063 TYP.	
0.600	1.000	0.024	0.039	
1.100	1.300	0.043	0.051	
0°	8°	0°	8°	
0.000	0.300	0.000	0.012	
5.350	TYP.	0.211 TYP.		
	Min. 2.200 0.000 0.660 0.460 6.500 5.100 4.830 6.000 2.186 9.800 2.900 1.400 1.600 0.600 1.100 0° 0.000	Min. Max. 2.200 2.400 0.000 0.127 0.660 0.860 0.460 0.580 6.500 6.700 5.100 5.460 4.830 TYP. 6.000 2.186 2.386 9.800 10.400 2.900 TYP. 1.700 1.600 TYP. 1.000 1.100 1.300 0° 8°	Min. Max. Min. 2.200 2.400 0.087 0.000 0.127 0.000 0.660 0.860 0.026 0.460 0.580 0.018 6.500 6.700 0.256 5.100 5.460 0.201 4.830 TYP. 0.190 6.000 6.200 0.236 2.186 2.386 0.086 9.800 10.400 0.386 2.900 TYP. 0.114 1.400 1.700 0.055 1.600 TYP. 0.063 0.600 1.000 0.024 1.100 1.300 0.043 0° 8° 0° 0.000 0.300 0.000	



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